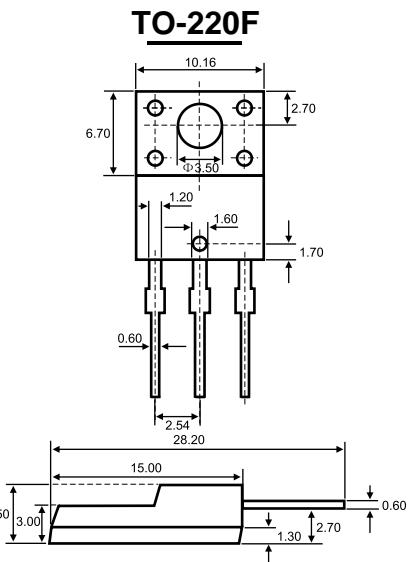

1. BASE
2. COLLECTOR
3. EMITTER
1 2 3


Features

- ◊ High Current Gain
 - ◊ Saturation Voltage Low
 - ◊ Power dissipation
- P_{cw} : 2 W (T_{amb}=25 °C)
25 W (T_{case}=25°C)

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Dimensions in inches and (millimeters)

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	3	A
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =1mA, I _E =0	80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =80V, I _E =0			10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =6V, I _C =0			10	μA
DC current gain	h _{FE} *	V _{CE} =4V, I _C =500mA	100		600	
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =3A, I _B =300mA			1	V
Transition frequency	f _T	V _{CE} =12V, I _C =200mA	7			MHz

*Pulse test: t_p≤300μS, δ≤0.02.

CLASSIFICATION OF h_{FE}

Rank	O	P	Q
Range	100-200	160-320	300-600

Typical Characteristics

